Audio Headset Analog Switch with Reduced GND Switch R_{ON} and FM Capability

GENERAL DESCRIPTION

The SGM3798 is an audio headset analog switch that is used to detect 3.5mm accessories and switch SLEEVE and RING2 by external controller. The ground signal is routed through a pair of low-impedance ground FETs (75m Ω TYP), resulting minimal impact on audio crosstalk performance. The ground FETs of the device are designed to allow FM signal pass-through, making it possible to use the ground line of the headset as an FM antenna in mobile audio application.

The SGM3798 is available in Green WLCSP-1.2×1.2-9B package. It operates over an ambient temperature range of -40°C to +85°C.

FEATURES

- Ground FET Switches R_{ON}: 75mΩ (TYP)
- High Isolation Microphone Line Switches
- Supports FM Signal Transmission Through the Ground FETs
- Reduction of Click-Pop Noise
- Power Supply Voltage Range: 2.6V to 5.0V
- Total Harmonic Distortion (MIC): 0.01% (TYP)
- Low Current Consumption: 2μA (TYP)
- -40°C to +85°C Operating Temperature Range
- Available in Green WLCSP-1.2×1.2-9B Package

APPLICATIONS

Mobile Phones/Tablet PCs Notebook/Ultrabook Computers

TYPICAL APPLICATION

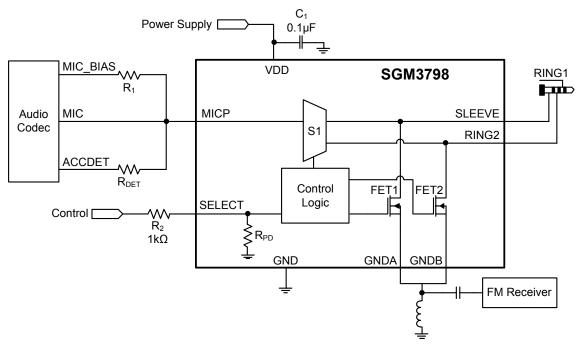


Figure 1. Typical Application Circuit



PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION	
SGM3798	WLCSP-1.2×1.2-9B	-40°C to +85°C	SGM3798YG/TR	3798 XXXX	Tape and Reel, 3000	

NOTE: XXXX = Date Code.

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

Voltage Range on VDD	0.3V to 6.0V
Voltage Range on SELECT, MICP, R	ING2, SLEEVE
	0.3V to V_{DD} + 0.3V
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility	
HBM	8000V
MM	300V
CDM	1500V

RECOMMENDED OPERATING CONDITIONS

Supply Voltage Range	2.6V to 5.0V
Operating Temperature Range	40°C to +85°C

OVERSTRESS CAUTION

Stresses beyond those listed may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational section of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

ESD SENSITIVITY CAUTION

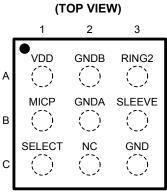
This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time.



PIN CONFIGURATION



WLCSP-1.2×1.2-9B

PIN DESCRIPTION

PIN	NAME	I/O	FUNCTION
A1	VDD	-	Power Supply for the Chip.
A2	GNDB	_	FET2 Ground Reference.
А3	RING2	I/O	Connected to the RING2 Segment of the Jack. This pin will be routed to MICP or GNDB depending on the logic level of SELECT pin.
B1	MICP	I/O	Microphone Signal Connection to Codec. Microphone bias should be fed into this pin.
B2	GNDA	_	FET1 Ground Reference.
В3	SLEEVE	I/O	Connected to the SLEEVE Segment of the Jack. This pin will be routed to MICP or GNDA depending on the logic level of SELECT pin.
C1	SELECT	I	The Logic Signal Used to Control S1 Switch, FET1 and FET2.
C2	NC	_	No Connection.
C3	GND	_	Chip Ground Reference.

S1 SWITCH

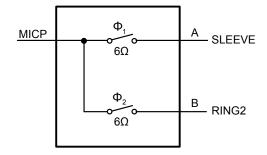


Figure 2. S1 Mux Detail

FUNCTION TABLE

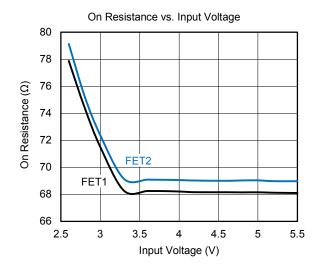
SELECT	FUNCTION				
0	MICP = A = SLEEVE, FET2 Turn On, FET1 Turn Off.				
1	MICP = B = RING2, FET2 Turn Off, FET1 Turn On.				

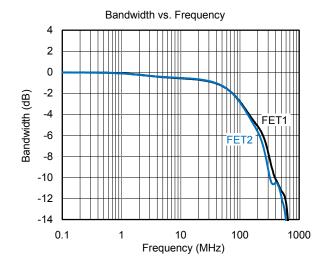
ELECTRICAL CHARACTERISTICS

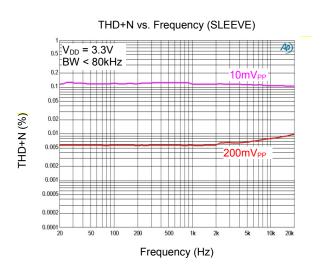
 $(V_{DD} = 2.6 \text{V to } 5.0 \text{V}, \text{ Full} = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}, \text{ typical values are at } V_{DD} = 3.3 \text{V}, T_{A} = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.})$

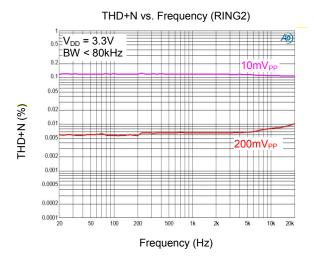
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS		
Input Voltage Range	V_{DD}		+25°C	2.6		5	V		
Quiescent Current	IQ	V _{DD} = 4.5V, V _{MICP} = 1.8V to V _{DD} , SELECT = Low or SELECT = High	+25°C		2	5	μA		
Lead (Outer 4.) /elferes Description		V _{DD} ≤ 3.3V	+25°C	0		V_{DD}	V		
Input/Output Voltage Range	V _{IO}	V _{DD} ≥ 3.3V	+25°C	0		3.3			
		V _{DD} = 2.6V	Full	1.3		V_{DD}	V		
Input Logic High for SELECT	V_{IH}	V _{DD} = 3.3V	Full	1.4		V_{DD}			
		V _{DD} = 4.5V	Full	1.55		V_{DD}			
		V _{DD} = 2.6V	Full	0		0.3	V		
Input Logic Low for SELECT	V_{IL}	V _{DD} = 3.3V	Full	0		0.4			
		V _{DD} = 4.5V	Full	0		0.5			
Pull Down Resistor of Select Pin	R_{PD}		+25°C		550		kΩ		
SWITCH RESISTANCE									
FET1 On Resistance	R _{F1}	$V_{DD} = 2.6V, V_{GND} = 0V, I_{GND} = 10mA$	+25°C		75	105	mΩ		
FET2 On Resistance	R _{F2}	V _{DD} - 2.0V, V _{GND} - 0V, I _{GND} - 10IIIA	+25°C		75	105	11122		
S1 On Resistance (Closed to A)	R _{S1A}	$V_{DD} = 2.6V, V_{SLEEVE/RING2} = 0V \text{ to } 2.6V,$	+25°C		6	7.5			
S1 On Resistance (Closed to B)	R _{S1B}	I _{MIC} = ±10mA			6	7.5	Ω		
SWITCH LEAKAGE CURRENT									
FET1, FET2 Off Leakage Current	I _{FET(OFF)}		+25°C			1	μΑ		
S1A, S1B Off Leakage Current	I _{S1AB(OFF)}	$V_{DD} = 5.5V$, $V_{IN} = 0V$ to 3.3V, $V_{OUT} = 0V$, SELECT = 0V to 5.5V				1	μΑ		
S1A, S1B On Leakage Current	I _{S1AB(ON)}					1	μΑ		
SWITCH DYNAMIC CHARACTERISTIC	cs				•	•			
FET1 Bandwidth	BW _{F1}	V 00mV 1 40mA	+25°C		100		MHz		
FET2 Bandwidth	BW _{F2}	$V = 60 \text{mV}_{PP}, I_{BIAS} = 10 \text{mA}$	+25°C		100		MHz		
		$V_{DD} = 2.6V, V_{AC} = 200 \text{mV}_{PP}, V_{DC} = 0V,$ $f = 217 \text{Hz}, R_S = R_L = 600 \Omega$ +25°C		100					
	PSRR	V_{DD} = 2.6V, V_{AC} = 200m V_{PP} , V_{DC} = 0V, f = 1kHz, R_S = R_L = 600 Ω		90					
Power Supply Rejection		V_{DD} = 2.6V, V_{AC} = 200m V_{PP} , V_{DC} = 0V, f = 20kHz, R_S = R_L = 600 Ω	+25°C		65		- dB		
т спот одрргу тојоског	. 5	V_{DD} = 5V, V_{AC} = 200m V_{PP} , V_{DC} = 0V, f = 217Hz, R_S = R_L = 600 Ω	+25°C		105				
		V_{DD} = 5V, V_{AC} = 200m V_{PP} , V_{DC} = 0V, f = 1kHz, R_S = R_L = 600 Ω	+25°C		100				
		V_{DD} = 5V, V_{AC} = 200m V_{PP} , V_{DC} = 0V, f = 20kHz, R_S = R_L = 600 Ω	+25°C		80				
SLEEVE or RING2 to MICP Isolation	ISO _{S1}	$V = 200 \text{mV}_{PP}, f = 20 \text{kHz}, R_L = 50 \Omega$	+25°C		-110		dB		
SLEEVE to RING2 Separation	SEP _{S1}	$V = 200 \text{mV}_{PP}, f = 20 \text{kHz}, R_L = 50 \Omega$	+25°C		-110		dB		
Total Harmonic Distortion	THD	V = 200m V_{PP} , f = 20-20kHz, R_S = 600 Ω , BW = 80kHz	+25°C		0.01		%		
DYNAMIC CHARACTERISTICS									
Turn-On Time	t _{ON}		+25°C		205		ns		
Turn-Off Time	t _{OFF}		+25°C		210		ns		
Break-Before-Make Time Delay	t _D		+25°C		27		ns		

TYPICAL PERFORMANCE CHARACTERISTICS



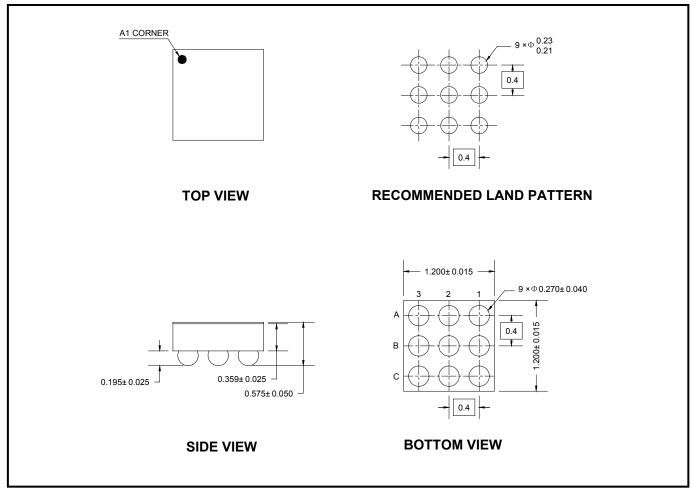






PACKAGE OUTLINE DIMENSIONS

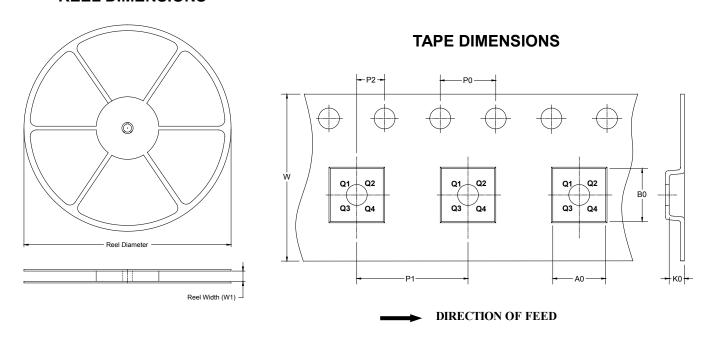
WLCSP-1.2×1.2-9B



NOTE: All linear dimensions are in millimeters.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

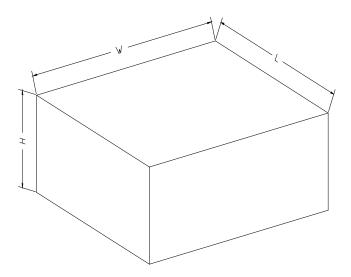


NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
WLCSP-1.2×1.2-9B	7"	9.5	1.35	1.35	0.73	4.0	4.0	2.0	8.0	Q1

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	3	
7" (Option)	368	227	224	8
7"	442	410	224	18



单击下面可查看定价,库存,交付和生命周期等信息

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